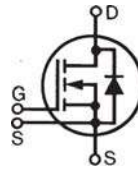


# Power MOSFET Single Die MOSFET

## IXFN230N10

N-Channel Enhancement Mode  
Avalanche Rated, High dv/dt, Low  $t_{rr}$



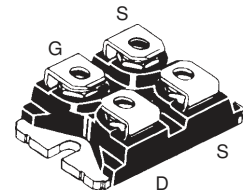
$$V_{DSS} = 100V$$

$$I_{D25} = 230A$$

$$R_{DS(on)} \leq 6.0m\Omega$$

$$t_{rr} \leq 250ns$$

miniBLOC, SOT-227 B  
E153432



G = Gate                      D = Drain  
S = Source

Either Source terminal at miniBLOC can be used as Main or Kelvin Source

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	100	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	100	V
$V_{GSS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ C$ , Chip capability	230	A
$I_{L(RMS)}$	External lead current limit	200	A
$I_{DM}$	$T_C = 25^\circ C$ , pulse width limited by $T_{JM}$	920	A
$I_A$	$T_C = 25^\circ C$	100	A
$E_{AS}$	$T_C = 25^\circ C$	4	J
$dv/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$	10	V/ns
$P_d$	$T_C = 25^\circ C$	700	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$V_{ISOL}$	50/60 Hz, RMS $t = 1min$ $I_{ISOL} \leq 1mA$ $t = 1s$	2500 3000	V~ V~
$M_d$	Mounting torque Terminal connection torque	1.5/13 1.3/11.5	Nm/lb.in. Nm/lb.in.
<b>Weight</b>		30	g

### Features

- International standard package
- miniBLOC, with Aluminium nitride isolation
- Low  $R_{DS(on)}$  HDMOST™ process
- Rugged polysilicon gate cell structure
- Avalanche rated
- Guaranteed FBSOA
- Low package inductance
- Fast intrinsic Rectifier

### Advantages

- Easy to mount
- Space savings
- High power density

### Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls

Symbol	Test Conditions ( $T_J = 25^\circ C$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 3mA$	100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 8mA$	2.0		V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ $V_{GS} = 0V$ $T_J = 125^\circ C$			100 $\mu A$ 2 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1			6.0 m $\Omega$

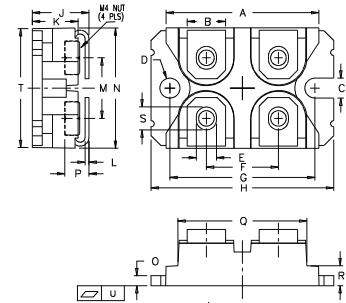
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{V}, I_D = 60\text{A}$ , Note 1	60	97	S
$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		19	nF
$C_{oss}$			5600	pF
$C_{rss}$			2750	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\Omega$ (External)		40	ns
$t_r$			150	ns
$t_{d(off)}$			112	ns
$t_f$			60	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		570	nC
$Q_{gs}$			70	nC
$Q_{gd}$			290	nC
$R_{thJC}$			0.18	$^\circ\text{C}/\text{W}$
$R_{thCS}$		0.05		$^\circ\text{C}/\text{W}$

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			230 A
$I_{SM}$	Repetitive, pulse width limited by $T_{JM}$			920 A
$V_{SD}$	$I_F = 100\text{A}, V_{GS} = 0\text{V}$ , Note 1			1.2 V
$t_{rr}$	$I_F = 50\text{A}, -di/dt = 100\text{A}/\mu\text{s}, V_R = 50\text{V}$			250 ns
$Q_{RM}$			1.2	$\mu\text{C}$
$I_{RM}$			9.0	A

Note 1: Pulse test,  $t \leq 300\mu\text{s}$ ; duty cycle,  $d \leq 2\%$ .

### miniBLOC, SOT-227 B

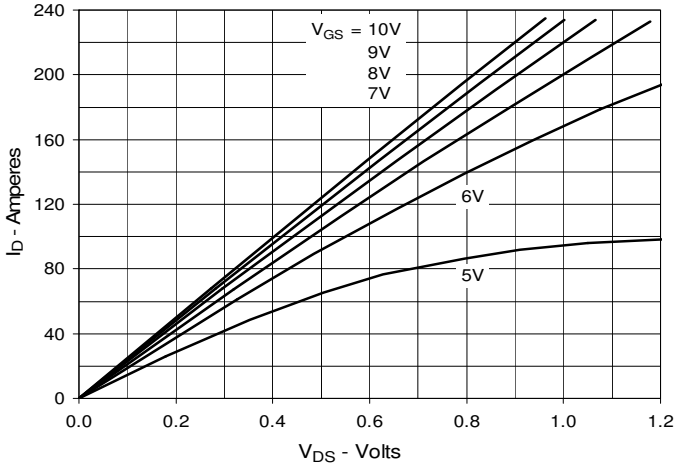
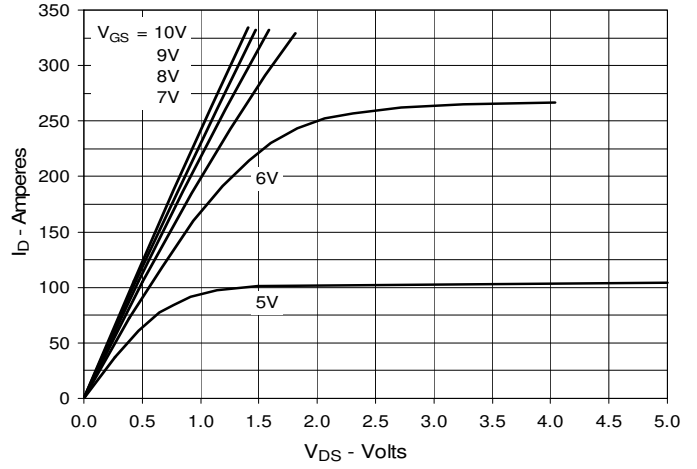
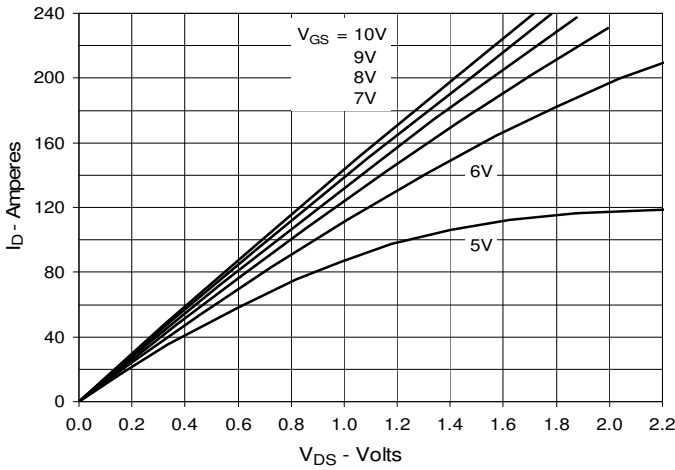
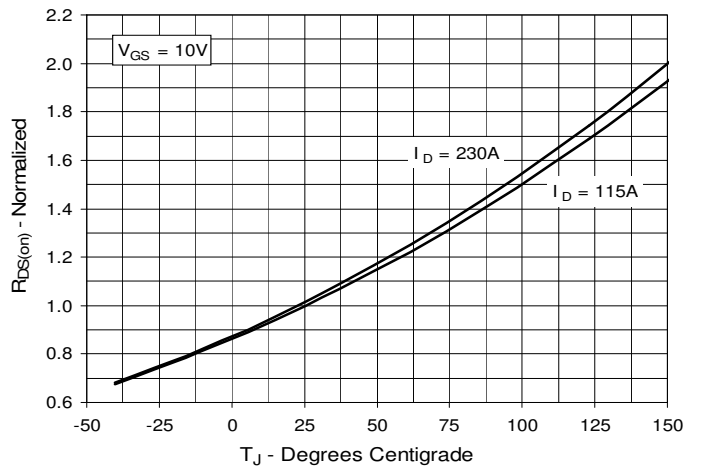
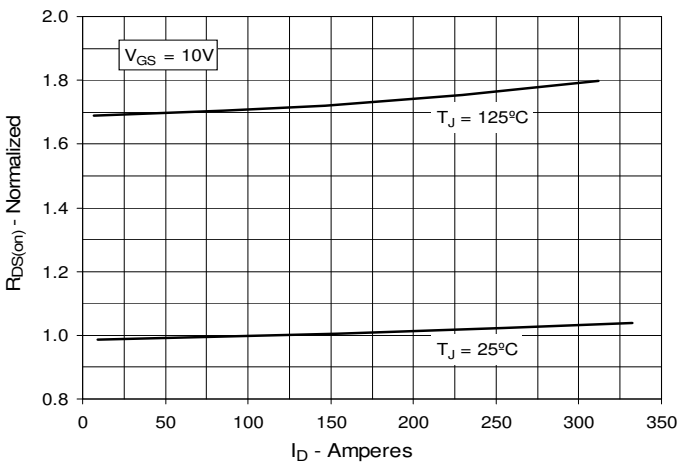
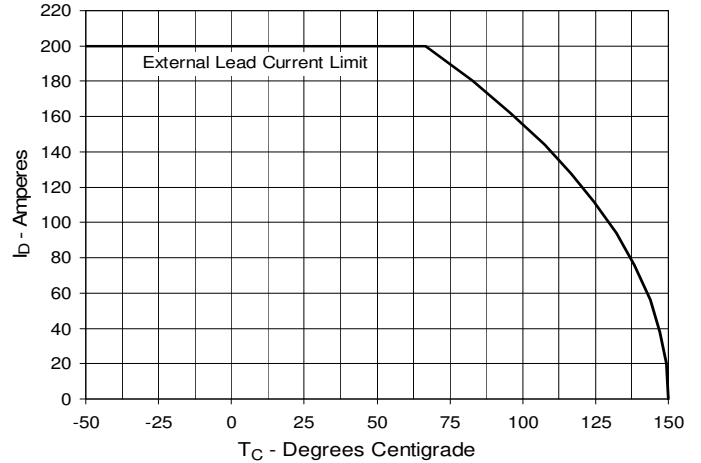


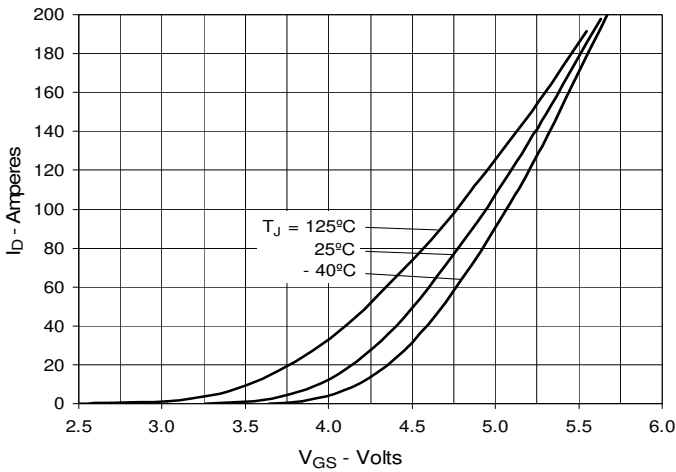
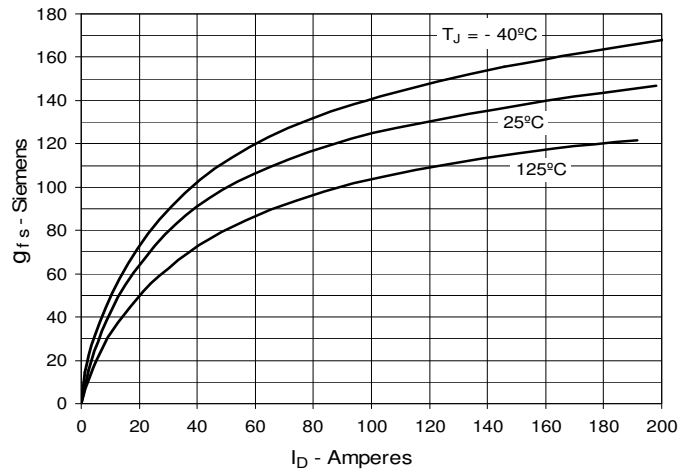
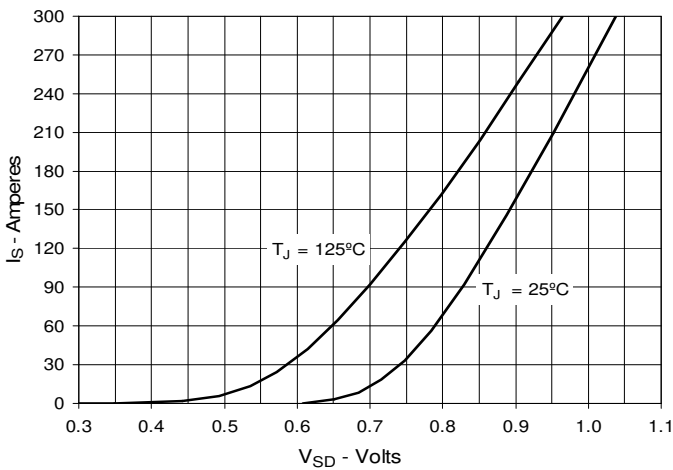
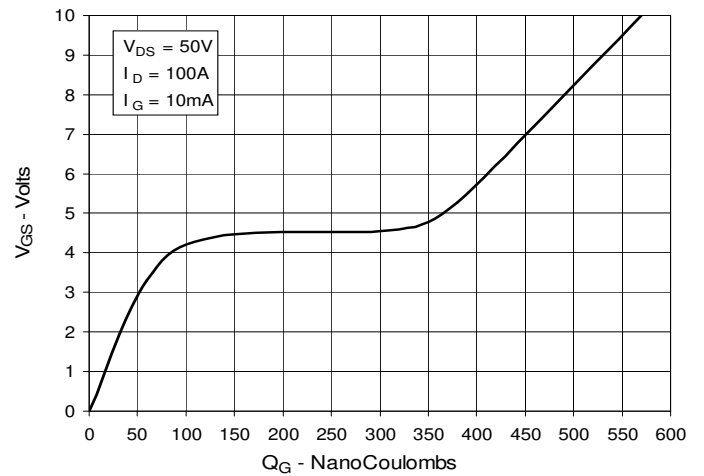
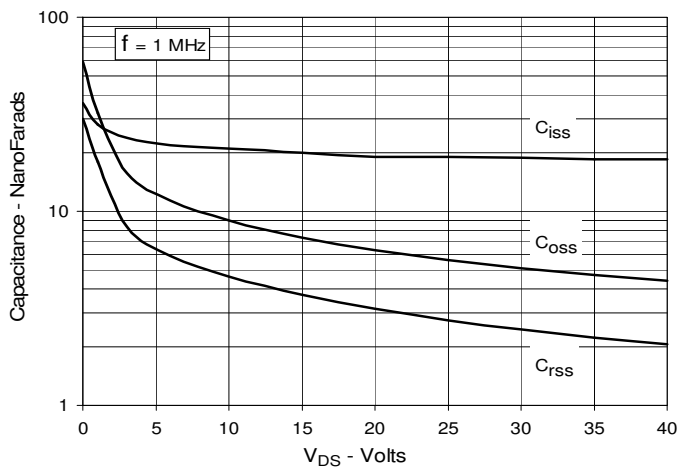
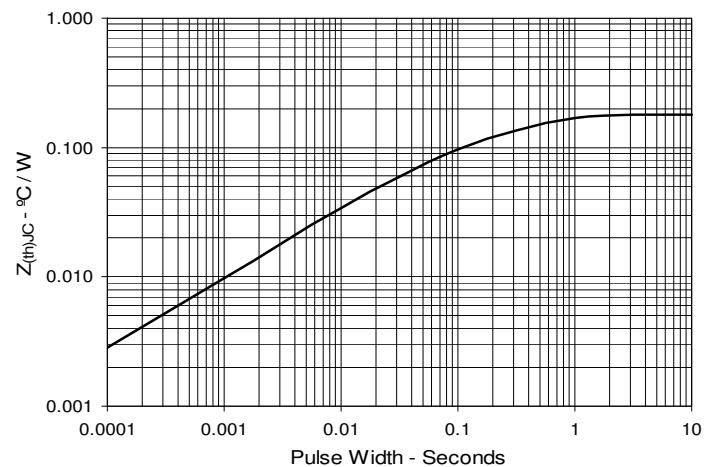
M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

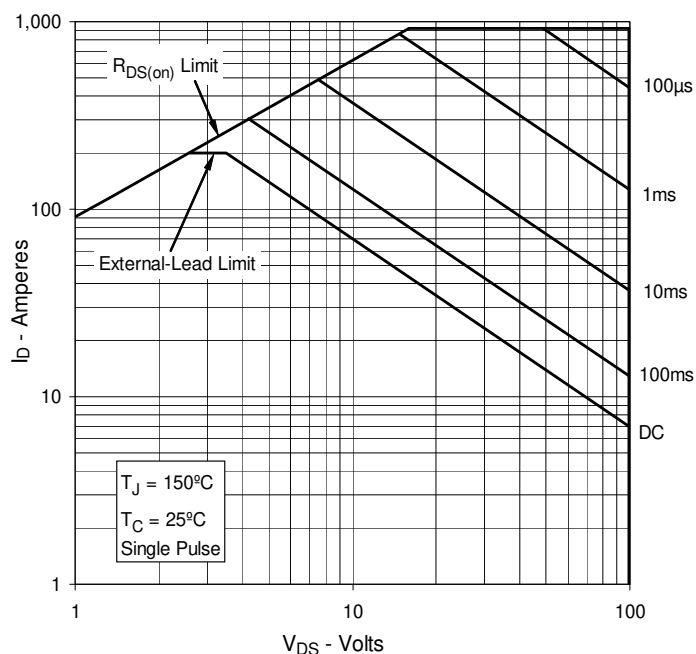
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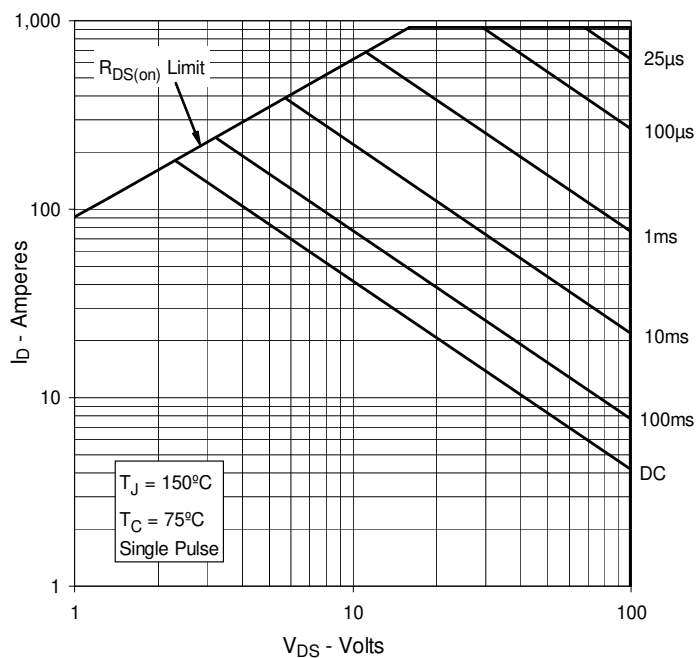
**Fig. 1. Output Characteristics  
@ 25°C**

**Fig. 2. Extended Output Characteristics  
@ 25°C**

**Fig. 3. Output Characteristics  
@ 125°C**

**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 115\text{A}$  Value  
vs. Junction Temperature**

**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 115\text{A}$  Value  
vs. Drain Current**

**Fig. 6. Maximum Drain Current vs.  
Case Temperature**


**Fig. 7. Input Admittance**

**Fig. 8. Transconductance**

**Fig. 9. Forward Voltage Drop of Intrinsic Diode**

**Fig. 10. Gate Charge**

**Fig. 11. Capacitance**

**Fig. 12. Maximum Transient Thermal Impedance**


**Fig. 13. Forward-Bias Safe Operating Area**  
@  $T_C = 25^\circ\text{C}$



**Fig. 14. Forward-Bias Safe Operating Area**  
@  $T_C = 75^\circ\text{C}$





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